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Claims 1-6(cancelled)

7. (Currently Amended) A system for processing a substrate, comprising:
- at least one atomic layer deposition barrier chamber for depositing a barrier layer comprising tantalum nitride, wherein the at least one atomic layer deposition barrier chamber comprises a first source providing PDMAT and a second source providing ammonia; and
 - at least one physical vapor deposition metal seed chamber for depositing a copper alloy seed layer over the barrier layer, wherein the copper alloy seed layer comprises copper and a metal selected from the group consisting of aluminum, magnesium, titanium, zirconium, tin, and combinations thereof and wherein the metal is present in the copper alloy in a concentration between about 0.01 atomic percent and about 2.0 atomic percent.

Claims 8-10(cancelled)

Claim 11. (Currently Amended) The system of claim 7, wherein the physical vapor deposition metal seed chamber is a high density plasma physical vapor deposition metal seed chamber.

Claim 12. (Currently Amended) The system of claim 7, further comprising one or more transfer chambers for transferring a substrate between the atomic layer deposition barrier chamber and the physical vapor deposition metal seed chamber.

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Claim 13 (cancelled)

14. ¹² (Currently Amended) A system for processing a substrate, comprising:
at least one atomic layer deposition barrier chamber for depositing a barrier layer comprising tantalum nitride, wherein the at least one atomic layer deposition barrier chamber comprises a first source providing PDMAT and a second source providing ammonia;

at least one physical vapor deposition copper alloy seed chamber for depositing a copper alloy seed layer over the barrier layer, wherein the copper alloy seed layer comprises copper and a metal selected from the group consisting of aluminum, magnesium, titanium, zirconium, tin, and combinations thereof[.]; and

at least one physical vapor deposition undoped copper seed chamber for depositing an undoped copper seed layer over the copper alloy seed layer.


Claims 15-18(cancelled)

19. (Previously Presented) The system of claim 14, wherein the physical vapor deposition copper alloy seed chamber is a high density plasma physical vapor deposition copper alloy seed chamber and the physical vapor deposition undoped copper seed chamber is a high density plasma physical vapor deposition undoped copper seed chamber.

20. (Previously Presented) The system of claim 14, further comprising one or more transfer chambers for transferring a substrate between the atomic layer deposition barrier chamber, the physical vapor deposition copper alloy seed chamber, and the physical vapor deposition undoped copper seed chamber.

Claim 21(cancelled)


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22.  (Previously Presented) A system for processing a substrate, comprising:
- at least one atomic layer deposition barrier chamber for depositing a barrier layer comprising tantalum nitride, wherein the at least one atomic layer deposition barrier chamber comprises a first source providing PDMAT and a second source providing ammonia;
 - at least one physical vapor deposition metal seed chamber for depositing a metal seed layer over the barrier layer, wherein the metal seed layer comprises a metal selected from the group consisting of aluminum, magnesium, titanium, zirconium, tin, and combinations thereof[.]; and
 - at least one physical vapor deposition undoped copper seed chamber for depositing an undoped copper seed layer over the metal seed layer.

Claims 23-26(cancelled)

27. (Previously Presented) The system of claim 22, wherein the physical vapor deposition metal seed chamber is a high density plasma physical vapor deposition metal seed chamber and the physical vapor deposition undoped copper seed chamber is a high density plasma physical vapor deposition undoped copper seed chamber.
28. (Previously Presented) The system of claim 22, further comprising one or more transfer chambers for transferring a substrate between the atomic layer deposition barrier chamber, the physical vapor deposition metal seed chamber, and the physical vapor deposition undoped copper seed chamber.

Claims 29-30(cancelled)

31.  (Previously Presented) The system of claim 7, wherein the copper alloy seed layer is deposited directly on the barrier layer comprising tantalum nitride.

Claims 32 and 33(cancelled)

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34. (Previously Presented) The system of claim 14, wherein the copper alloy seed layer is deposited directly on the barrier layer comprising tantalum nitride.

Claims 35 and 36(cancelled)

37. (Previously Presented) The system of claim 22, wherein the metal seed layer is deposited directly on the barrier layer comprising tantalum nitride.

Claim 38(cancelled)

39. (Previously Presented) The system of claim 7, wherein the copper alloy seed layer comprises the metal present in the copper alloy in a concentration between about 0.1 atomic percent and about 1.0 atomic percent.

40. (Previously Presented) The system of claim 7, wherein the atomic layer deposition barrier chamber comprises a first source providing a tantalum containing compound and a second source providing a nitrogen containing compound.

Claim 41(cancelled)

42. (Previously Presented) The system of claim 7, wherein the copper alloy seed layer comprises copper and aluminum.

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43. (Previously Presented) The system of claim 7, wherein the copper alloy seed layer comprises copper and titanium.

44. (Previously Presented) The system of claim 14, wherein the copper alloy seed layer comprises the metal present in the copper alloy in a concentration between about 0.001 atomic percent and about 5.0 atomic percent.

45. (Previously Presented) The system of claim 14, wherein the copper alloy seed layer comprises the metal present in the copper alloy in a concentration between about 0.01 atomic percent and about 2.0 atomic percent.

46. (Previously Presented) The system of claim 14, wherein the atomic layer deposition barrier chamber comprises a first source providing a tantalum containing compound and a second source providing a nitrogen containing compound.

Claim 47(cancelled)

48. (Previously Presented) The system of claim 14, wherein the copper alloy seed layer comprises copper and aluminum.

49. (Previously Presented) The system of claim 14, wherein the copper alloy seed layer comprises copper and titanium.

Claims 50 and 51(cancelled)

52. (Currently Amended) A system for processing a substrate, comprising:

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at least one atomic layer deposition barrier chamber comprising a first source providing a ~~tantalum-containing compound~~ PDMAT and a second source providing a nitrogen containing compound;

at least one physical vapor deposition metal seed chamber having a copper alloy target comprising copper and a metal selected from the group consisting of aluminum, titanium, and combinations thereof and wherein the metal is present in the copper alloy target in a concentration between about 0.001 atomic percent and about 5.0 atomic percent; and

at least one transfer chamber for transferring the substrate between the atomic layer deposition barrier chamber and the physical vapor deposition metal seed chamber.

53. (Previously Presented) The system of claim 52, wherein the metal is present in the copper alloy target in a concentration between about 0.01 atomic percent and about 2.0 atomic percent.

54. (Previously Presented) The system of claim 53, wherein the metal is present in the copper alloy target in a concentration between about 0.1 atomic percent and about 1.0 atomic percent.

55. (Previously Presented) The system of claim 53, wherein the copper alloy target consists essentially of copper and aluminum.

56. (Previously Presented) The system of claim 53, wherein the copper alloy target consists essentially of copper and titanium.

57. (Currently Amended) The system of claim 52, wherein the ~~first source of the atomic layer deposition barrier chamber provides PDMAT and the second source of the atomic layer deposition barrier chamber provides~~ nitrogen containing compound is ammonia.

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58. (New) The system of claim 7, wherein the PDMAT has a chlorine concentration of about 5 ppm or less.

59. (New) The system of claim 14, wherein the PDMAT has a chlorine concentration of about 5 ppm or less.

60. (New) The system of claim 22, wherein the PDMAT has a chlorine concentration of about 5 ppm or less.

61. (New) The system of claim 52, wherein the PDMAT has a chlorine concentration of about 5 ppm or less.